# 2SC6054J

### Silicon NPN epitaxial planar type

For general amplification Complementary to 2SA2174J

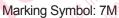
#### Features

- High forward current transfer ratio h<sub>FE</sub>
- SS-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing.

Unit: mm $1.60^{+0.05}_{-0.03}$ $50^{+}_{-0.01}$ $0.12^{+0.03}_{-0.01}$ $0.12^{+0.01}_{-0.01}$ $0.12^{+0.01}_{-0.01}$ $0.12^{+0.01}_{-0.01}$ $0.12^{+0.01}_{-0.01}$ $0.12^{+0.01}_{-0.01}$ $0.12^{+0.01}_{-0.$
1: Base 2: Emitter 3: Collector SSMini3-F1 Package

#### Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	60	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	50	V	
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	7	V	
Collector current	I <sub>C</sub>	100	mA	
Peak collector current	I <sub>CP</sub>	200	mA	
Collector power dissipation	P <sub>C</sub>	125	mW	N
Junction temperature	Tj	125	°C	
Storage temperature	T <sub>stg</sub>	-55 to +125	°C	
Electrical Characteristics $T_a = 2$	5°C±3°C			

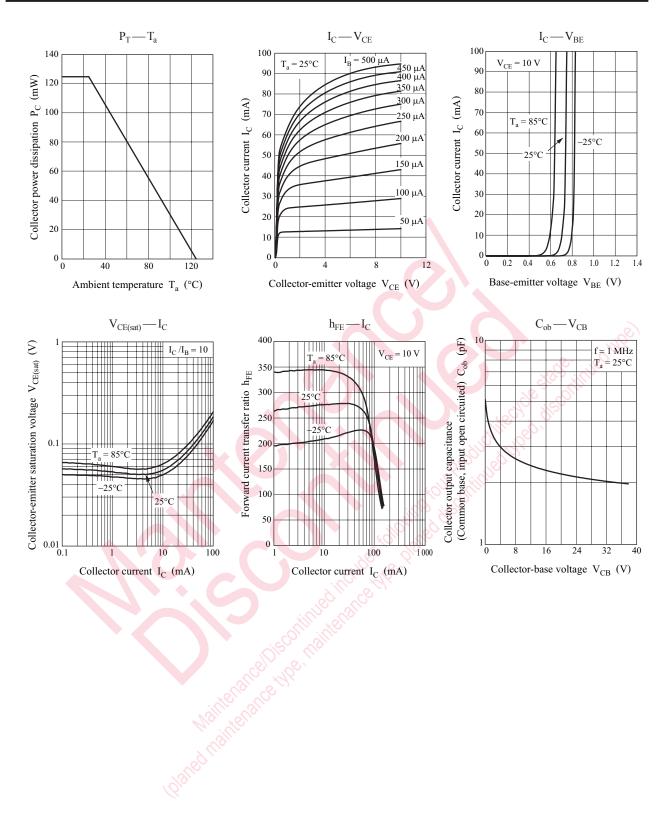


#### Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_{\rm C} = 10 \ \mu {\rm A}, I_{\rm E} = 0$	60			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = 2  {\rm mA}, I_{\rm B} = 0$	50			V
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	$I_{\rm E} = 10 \mu {\rm A}, I_{\rm C} = 0$	7			V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = 20 V, I_E = 0$			0.1	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = 10 \text{ V}, I_{B} = 0$			100	μΑ
Forward current transfer ratio	h <sub>FE</sub>	$V_{CE} = 10 \text{ V}, I_C = 2 \text{ mA}$	160		460	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = 100 \text{ mA}, I_{\rm B} = 10 \text{ mA}$		0.1	0.3	V
Transition frequency	f <sub>T</sub>	$V_{CB} = 10 \text{ V}, I_E = -2 \text{ mA}, f = 200 \text{ MHz}$		100		MHz
Collector output capacitance (Common base, input open circuited)	C <sub>ob</sub>	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		2.2		pF

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

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